



SM Technology Co., Limited

SOT-23 Plastic-Encapsulate Transistors

MMBTA42 TRANSISTOR (NPN)

FEATURES

- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary to MMBTA92 (PNP)

SOT-23

1. BASE
2. Emitter
3. COLLECTOR



MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.3	A
P_c	Collector Power dissipation	0.35	W
R_{eJA}	Thermal Resistance, junction to Ambient	357	°C/mW
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

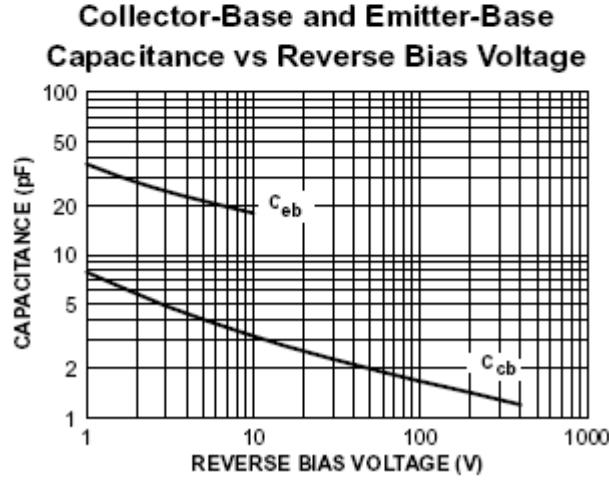
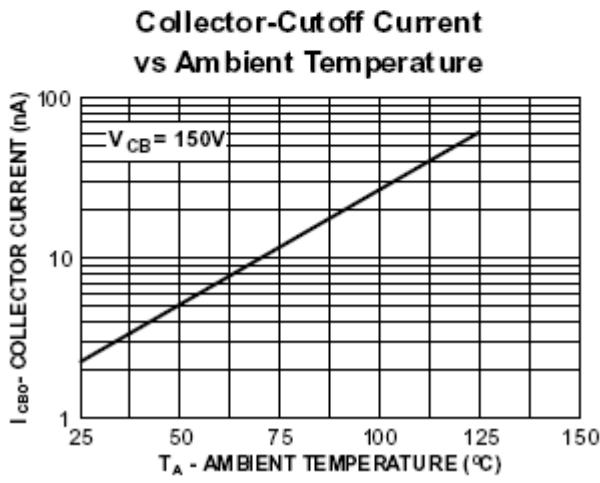
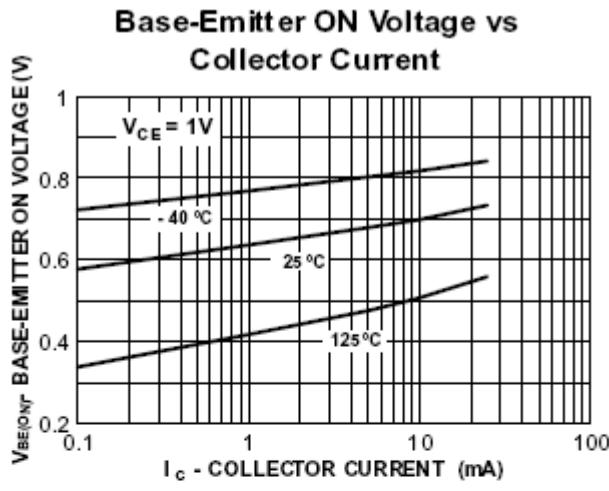
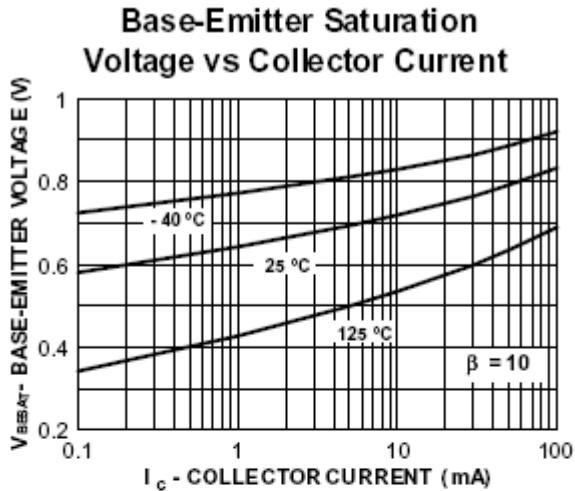
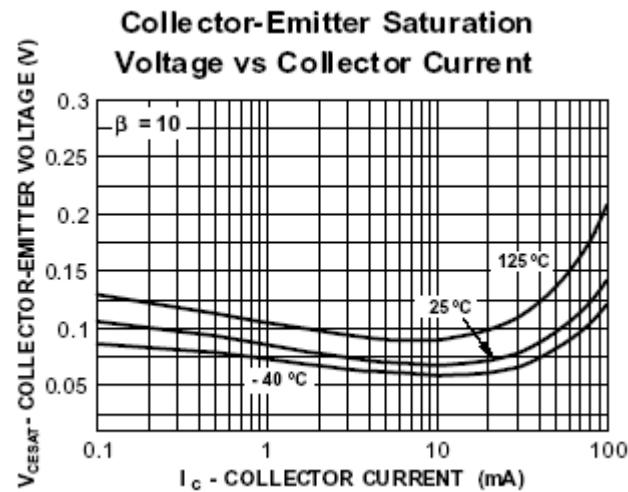
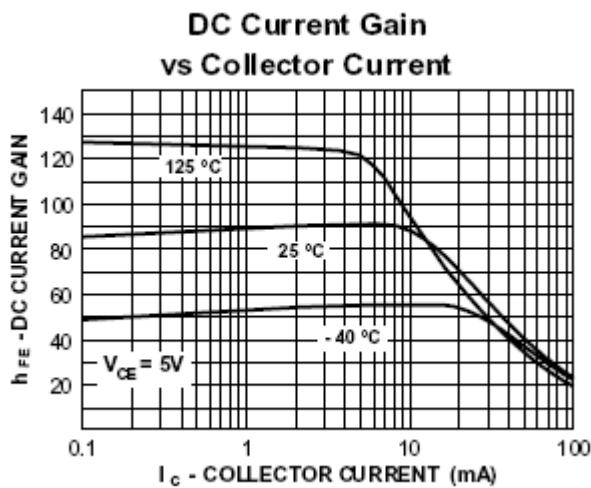
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C= 100\mu\text{A}, I_E=0$	300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C= 1\text{mA}, I_B=0$	300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E= 100\mu\text{A}, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=200\text{V}, I_E=0$		0.25	μA
Emitter cut-off current	I_{EBO}	$V_{EB}= 5\text{V}, I_C=0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}= 10\text{V}, I_C= 1\text{mA}$	60		
	$h_{FE(2)}$	$V_{CE}= 10\text{V}, I_C= 10\text{mA}$	100	200	
	$h_{FE(3)}$	$V_{CE}= 10\text{V}, I_C= 30\text{mA}$	60		
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C= 20\text{mA}, I_B= 2\text{mA}$		0.2	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C= 20\text{mA}, I_B= 2\text{mA}$		0.9	V
Transition frequency	f_T	$V_{CE}= 20\text{V}, I_C= 10\text{mA}, f=30\text{MHz}$	50		MHz



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Typical Characteristics

MMBT42



MMBTA42



RoHS
COMPLIANCE

Power Dissipation vs
Ambient Temperature

